74AUP2G07 Low-power dual buffer with open-drain output Rev. 7 – 29 November 2012

**Product data sheet** 

### 1. General description

The 74AUP2G07 provides two non-inverting buffers with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static-power consumption; I<sub>CC</sub> = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power dual buffer with open-drain output

### 3. Ordering information

Table 1. Ordering information									
Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G07GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886					
74AUP2G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891					
74AUP2G07GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP2G07GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202					

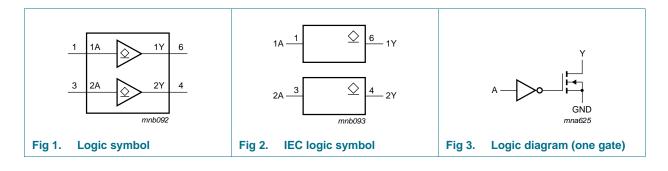
### 4. Marking

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Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AUP2G07GW	р7
74AUP2G07GM	р7
74AUP2G07GF	р7
74AUP2G07GN	р7
74AUP2G07GS	р7

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

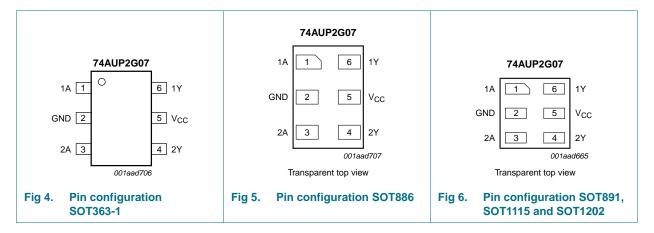
### 5. Functional diagram



Low-power dual buffer with open-drain output

### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

### 7. Functional description

Table 4.   Function table <sup>[1]</sup>	
Input	Output
nA	nY
L	L
Н	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF state.

Low-power dual buffer with open-drain output

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	20	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

....

[2] For SC-88 package: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

Table 6.	Recommended operating condition	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	0	200	ns/V

### **10. Static characteristics**

#### Table 7.Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35\times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V

 74AUP2G07
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 Product data sheet
 Rev. 7 — 29 November 2012
 4 of 18

### **NXP Semiconductors**

## 74AUP2G07

Low-power dual buffer with open-drain output

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I <sub>OZ</sub>	OFF-state output current	$V_{\rm I}$ = $V_{\rm IH};$ $V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \text{ to } 3.6 \ V \end{array}$	-	-	0.5	μA
∆l <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_I$ = GND or $V_{CC}$	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I <sub>OZ</sub>	OFF-state output current	$V_{\rm I}$ = $V_{\rm IH};$ $V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μA

#### Table 7. Static characteristics ...continued

At recommended operating conditions: voltages are referenced to GND (ground = 0 V).

 Product data sheet
 Rev. 7 — 29 November 2012
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#### Low-power dual buffer with open-drain output

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
lcc	supply current		-	-	0.9	μA
Δl <sub>CC</sub>	additional supply current	$V_{I}$ = $V_{CC}$ $-$ 0.6 V; $I_{O}$ = 0 A; $V_{CC}$ = 3.3 V	-	-	50	μΑ
T <sub>amb</sub> = –	40 °C to +125 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70\times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	-	-	$0.30\times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_{O}$ = 1.1 mA; $V_{CC}$ = 1.1 V	-	-	$0.33\times V_{CC}$	V
		$I_{O}$ = 1.7 mA; $V_{CC}$ = 1.4 V	-	-	0.41	V
		$I_{O}$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.36	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 3.0 V	-	-	0.50	V
l	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μΑ
l <sub>oz</sub>	OFF-state output current	$V_{\rm I}$ = $V_{\rm IH};$ $V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	$V_{I}$ or $V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μΑ
∆l <sub>OFF</sub>	additional power-off leakage current		-	-	±0.75	μA
сс	supply current	$      V_{I} = \text{GND or } V_{\text{CC}}; I_{\text{O}} = 0 \text{ A};                                   $	-	-	1.4	μA
∆l <sub>CC</sub>	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

#### Table 7. Static characteristics ... continued

74AUP2G07 Product data sheet

Rev. 7 — 29 November 2012

Low-power dual buffer with open-drain output

### **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C	25 °C		–40 °C to +125 °C		
				Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F								
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]						
		$V_{CC} = 0.8 V$	-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	2.1	4.1	7.5	1.7	9.1	10.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.6	3.0	5.1	1.3	6.1	6.7	ns
		$V_{CC}$ = 1.65 V to 1.95 V	1.6	2.7	4.0	1.2	5.0	5.5	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.1	2.1	3.2	0.9	4.0	4.4	ns
		$V_{CC}$ = 3.0 V to 3.6 V	1.4	2.2	2.8	1.1	3.3	3.6	ns
C <sub>L</sub> = 10	pF								
pd	propagation delay	nA to nY; see Figure 7	[2]						
		$V_{CC} = 0.8 V$	-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.3	3.8	6.1	2.0	7.4	8.1	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.4	3.6	4.8	1.8	6.1	6.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	2.8	3.8	1.3	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.2	3.1	4.2	1.6	4.5	5.0	ns
C <sub>L</sub> = 15	pF								
pd	propagation delay	nA to nY; see Figure 7	[2]						
		$V_{CC} = 0.8 V$	-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	3.0	4.5	6.8	2.6	8.6	9.4	ns
		$V_{CC}$ = 1.65 V to 1.95 V	2.8	4.4	6.7	2.2	7.8	8.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V	2.4	3.4	4.5	1.9	5.3	5.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.2	4.0	5.7	1.9	6.1	6.7	ns
C <sub>L</sub> = 30	pF								
pd	propagation delay	nA to nY; see Figure 7	[2]						
		$V_{CC} = 0.8 V$	-	26.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	4.8	9.0	15.6	4.3	18.8	20.7	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	4.1	6.7	9.4	3.7	11.8	13.0	ns
		$V_{CC}$ = 1.65 V to 1.95 V	3.8	6.8	9.7	3.2	11.0	12.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V	3.7	5.2	6.7	3.0	7.1	7.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	3.6	6.4	9.7	2.8	10.4	11.4	ns

#### Low-power dual buffer with open-drain output

Symbol	Parameter	Conditions		25 °C			0 °C to +′	125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F, 10 pF, 15 pF and	30 pF							
	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	8 <u>][4]</u>						
		$V_{CC} = 0.8 V$	-	0.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	-	0.6	-	-	-	-	pF
		$V_{CC}$ = 1.4 V to 1.6 V	-	0.6	-	-	-	-	pF
		$V_{CC}$ = 1.65 V to 1.95 V	-	0.7	-	-	-	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V	-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	1.2	-	-	-	-	pF

#### Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

[1] All typical values are measured at nominal  $V_{CC}$ .

[2]  $t_{pd}$  is the same as  $t_{PZL}$  and  $t_{PLZ}$ .

[3] All specified values are the average typical values over all stated loads.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$  where:

f<sub>i</sub> = input frequency in MHz;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching.

### 12. Waveforms

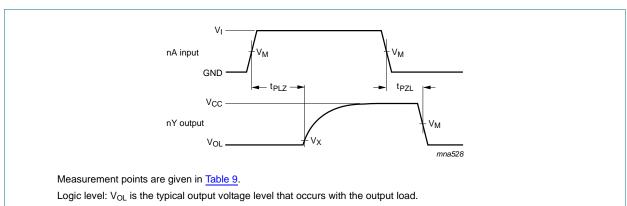


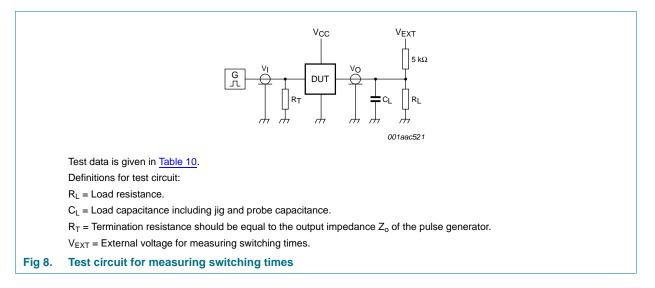
Fig 7. The data input (nA) to output (nY) propagation delays

#### Table 9.Measurement points

Supply voltage	Input	Output	
V <sub>cc</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>
0.8 V to 1.6 V	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$	V <sub>OL</sub> + 0.1 V
1.65 V to 2.7 V	$0.5\times V_{CC}$	$0.5  imes V_{CC}$	V <sub>OL</sub> + 0.15 V
3.0 V to 3.6 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	V <sub>OL</sub> + 0.3 V

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Product data sheet	Rev. 7 — 29 November 2012	8 of 18

#### Low-power dual buffer with open-drain output



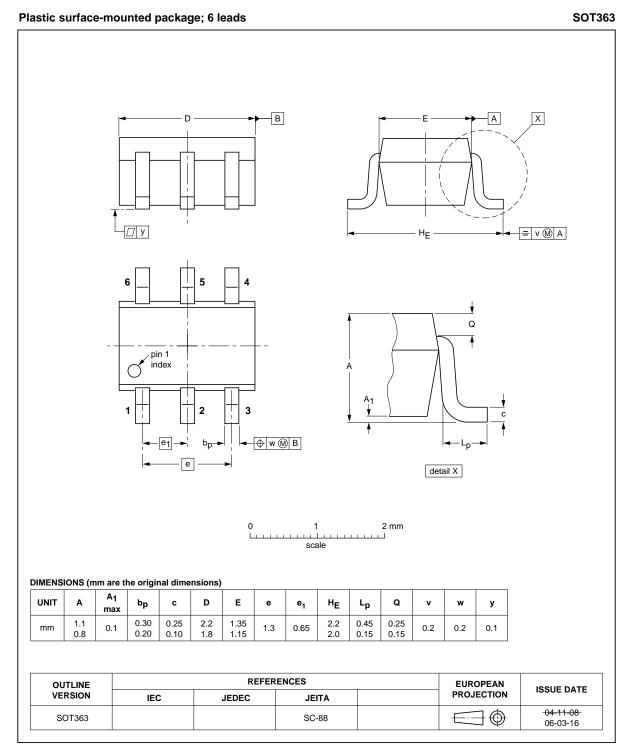
#### Table 10. Test data

Supply voltage	Supply voltage Input		Load		V <sub>EXT</sub>		
V <sub>cc</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL <sup>[1]</sup>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	V <sub>CC</sub>	≤ 3 ns	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, set-up and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

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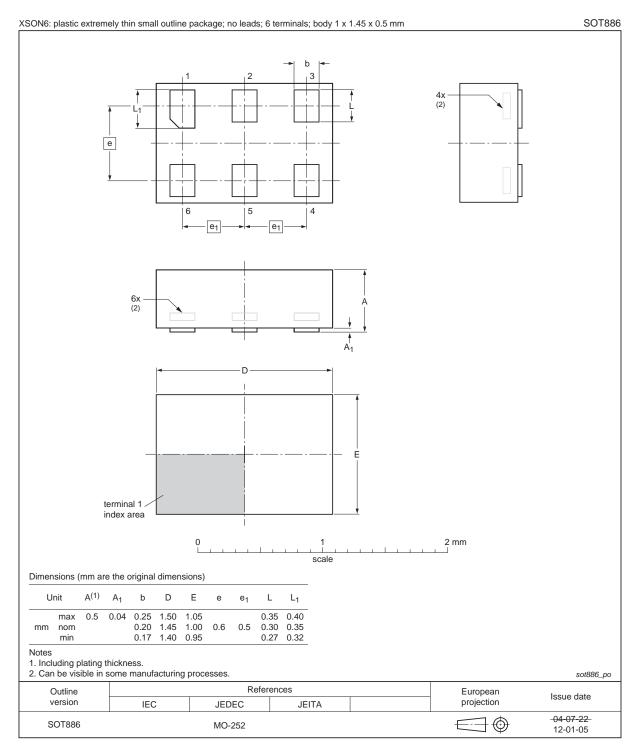
### 13. Package outline



#### Fig 9. Package outline SOT363 (SC-88)

74AUP2G07 Product data sheet

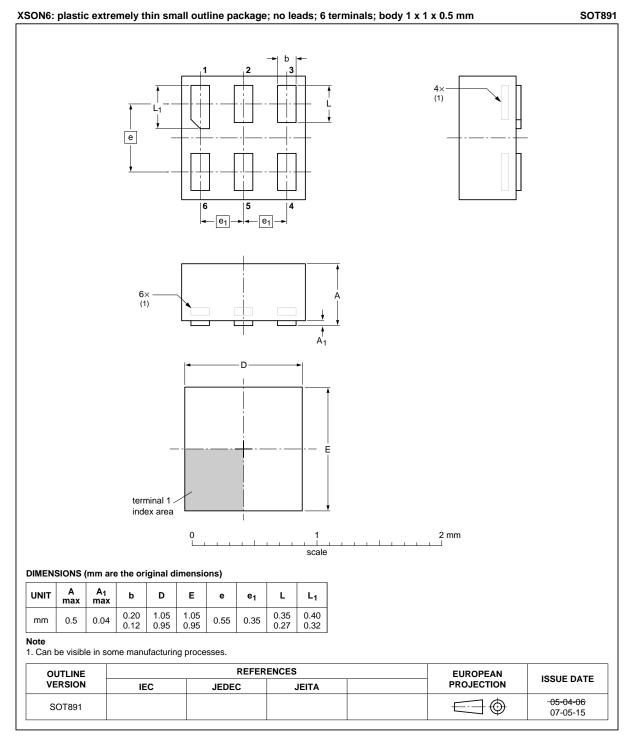
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#### Fig 10. Package outline SOT886 (XSON6)

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Product data sheet	Rev. 7 — 29 November 2012	11 of 18

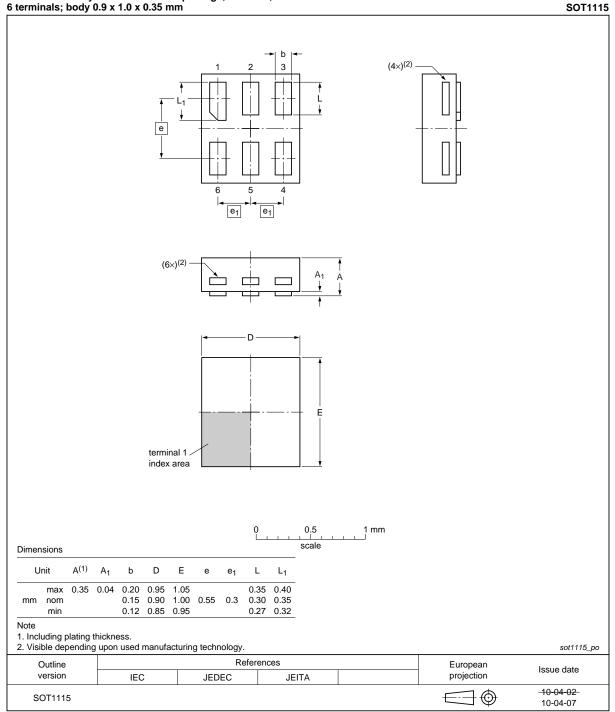
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### Fig 11. Package outline SOT891 (XSON6)

74AUP2G07 Product data sheet

Low-power dual buffer with open-drain output

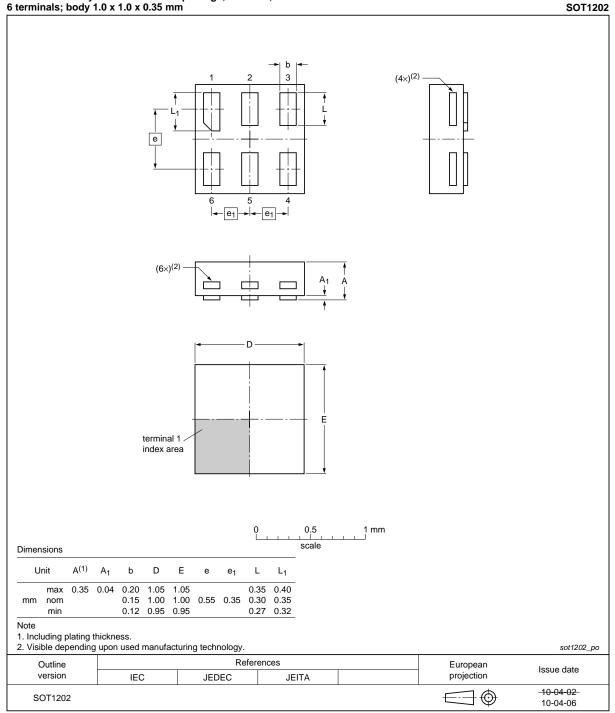


## XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 12. Package outline SOT1115 (XSON6)

74AUP2G07 **Product data sheet** 

Low-power dual buffer with open-drain output



## XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1202 (XSON6)

74AUP2G07 **Product data sheet** 

Low-power dual buffer with open-drain output

## 14. Abbreviations

AcronymDescriptionCDMCharged Device ModelDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Table 11. Abbreviations				
DUT     Device Under Test       ESD     ElectroStatic Discharge       HBM     Human Body Model	Acronym	Description			
ESD     ElectroStatic Discharge       HBM     Human Body Model	CDM	Charged Device Model			
HBM Human Body Model	DUT	Device Under Test			
	ESD	ElectroStatic Discharge			
MM Machine Model	HBM	Human Body Model			
	MM	Machine Model			

## 15. Revision history

Table 12. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G07 v.7	20121129	Product data sheet	-	74AUP2G07 v.6
Modifications:	<ul> <li>Package ou</li> </ul>	tline drawing of SOT886 (	Figure 10) modified.	
74AUP2G07 v.6	20111202	Product data sheet	-	74AUP2G07 v.5
74AUP2G07 v.5	20100909	Product data sheet	-	74AUP2G07 v.4
74AUP2G07 v.4	20090611	Product data sheet	-	74AUP2G07 v.3
74AUP2G07 v.3	20071016	Product data sheet	-	74AUP2G07 v.2
74AUP2G07 v.2	20070612	Product data sheet	-	74AUP2G07 v.1
74AUP2G07 v.1	20061121	Product data sheet	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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74AUP2G07

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Product data sheet

#### Low-power dual buffer with open-drain output

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#### Low-power dual buffer with open-drain output

### **18. Contents**

1	General description	1
2	Features and benefits	1
3	Ordering information	2
4	Marking	2
5	Functional diagram	2
6	Pinning information	3
6.1 6.2	Pinning	
7	Functional description	3
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	4
11	Dynamic characteristics	7
12	Waveforms	8
13	Package outline	10
14	Abbreviations	15
15	Revision history	15
16	Legal information	16
16.1	Data sheet status	16
16.2	Definitions	16
16.3		16
16.4	Trademarks	17
17	Contact information	17
18	Contents	18

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